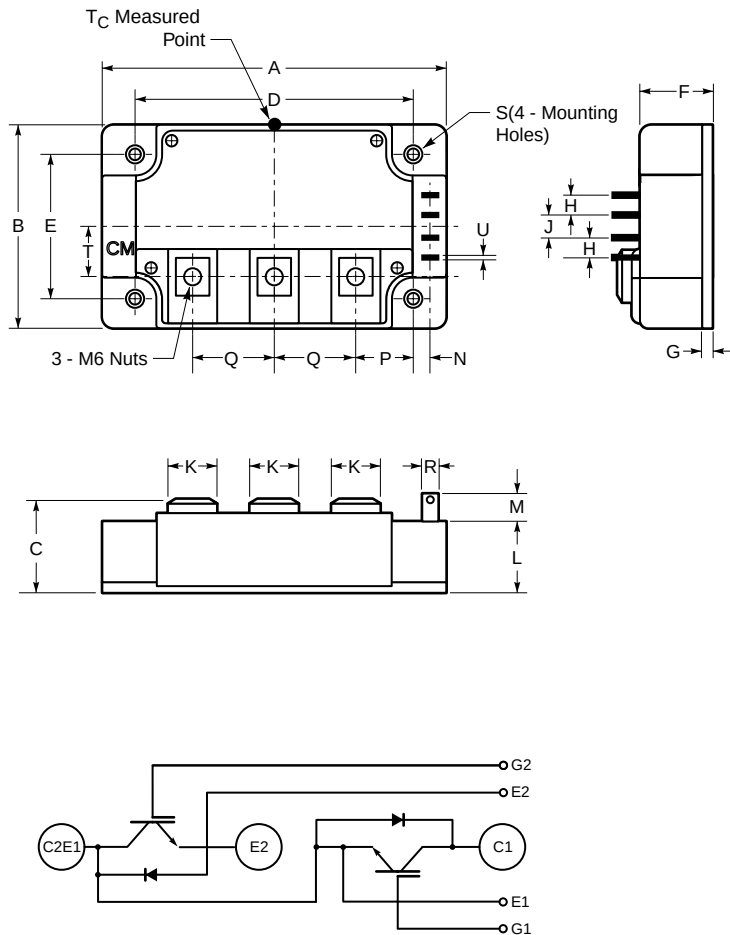


MITSUBISHI IGBT MODULES
CM200DU-24H
 HIGH POWER SWITCHING USE
 INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.25	108.0
B	2.44	62.0
C	1.14 +0.04/-0.02	29 +1.0/-0.5
D	3.66±0.01	93.0±0.25
E	1.88±0.01	48.0±0.25
F	0.87	22.0
G	0.16	4.0
H	0.24	6.0
J	0.59	15.0

Dimensions	Inches	Millimeters
K	0.71	18.0
L	0.87	22.0
M	0.33	8.5
N	0.10	2.5
P	0.85	21.5
Q	0.98	25.0
R	0.11	2.8
S	0.25 Dia.	6.5 Dia.
T	0.6	15.15



Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of two IGBTs in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM200DU-24H is a 1200V (V_{CES}), 200 Ampere Dual IGBT Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	200	24

CM200DU-24H

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	Symbol	Ratings	Units
Junction Temperature	T_j	-40 to 150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^{\circ}\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_c = 25^{\circ}\text{C}$)	I_c	200	Amperes
Peak Collector Current ($T_j \leq 150^{\circ}\text{C}$)	I_{CM}	400*	Amperes
Emitter Current** ($T_c = 25^{\circ}\text{C}$)	I_E	200	Amperes
Peak Emitter Current**	I_{EM}	400*	Amperes
Maximum Collector Dissipation ($T_c = 25^{\circ}\text{C}$)	P_c	1130	Watts
Mounting Torque, M6 Main Terminal	—	3.5~4.5	N · m
Mounting Torque, M6 Mounting	—	3.5~4.5	N · m
Weight	—	400	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Vrms

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{\text{CE}} = V_{\text{CES}}, V_{\text{GE}} = 0\text{V}$	—	—	1	mA
Gate Leakage Voltage	I_{GES}	$V_{\text{GE}} = V_{\text{GES}}, V_{\text{CE}} = 0\text{V}$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_c = 20\text{mA}, V_{\text{CE}} = 10\text{V}$	4.5	6	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_c = 200\text{A}, V_{\text{GE}} = 15\text{V}, T_j = 25^{\circ}\text{C}$	—	2.9	3.7	Volts
		$I_c = 200\text{A}, V_{\text{GE}} = 15\text{V}, T_j = 125^{\circ}\text{C}$	—	2.85	—	Volts
Total Gate Charge	Q_G	$V_{\text{CC}} = 600\text{V}, I_c = 200\text{A}, V_{\text{GE}} = 15\text{V}$	—	750	—	nC
Emitter-Collector Voltage*	V_{EC}	$I_E = 200\text{A}, V_{\text{GE}} = 0\text{V}$	—	—	3.2	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.Dynamic Electrical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0V	—	—	30	nF
Output Capacitance		C _{oes}		—	—	10.5	nF
Reverse Transfer Capacitance		C _{res}		—	—	6	nF
Resistive Load	Turn-on Delay Time	t _{d(on)}	V _{CC} = 600V, I _C = 200A,	—	—	200	ns
	Rise Time	t _r	V _{GE1} = V _{GE2} = 15V,	—	—	300	ns
Switch Times	Turn-off Delay Time	t _{d(off)}	R _G = 1.6Ω, Resistive	—	—	300	ns
	Fall Time	t _f	Load Switching Operation	—	—	350	ns
Diode Reverse Recovery Time		t _{rr}	I _E = 200A, di _E /dt = -400A/μs	—	—	300	ns
Diode Reverse Recovery Charge		Q _{rr}	I _E = 200A, di _E /dt = -400A/μs	—	1.1	—	μC

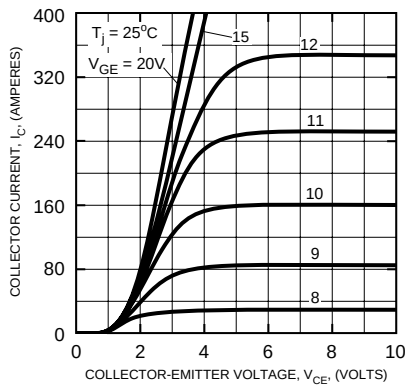
Thermal and Mechanical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)Q}}$	Per IGBT 1/2 Module	—	—	0.11	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)D}}$	Per FWDi 1/2 Module	—	—	0.18	$^{\circ}\text{C}/\text{W}$
Contact Thermal Resistance	$R_{\text{th(c-f)}}$	Per Module, Thermal Grease Applied	—	0.020	—	$^{\circ}\text{C}/\text{W}$

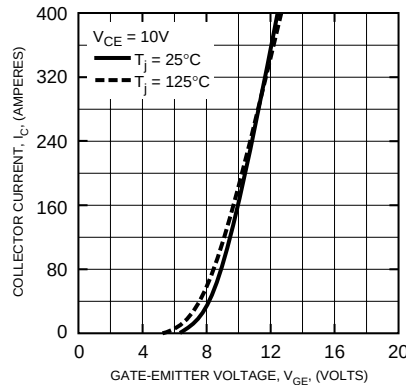
CM200DU-24H

HIGH POWER SWITCHING USE
INSULATED TYPE

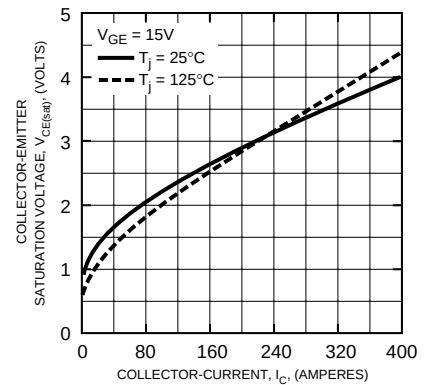
OUTPUT CHARACTERISTICS
(TYPICAL)



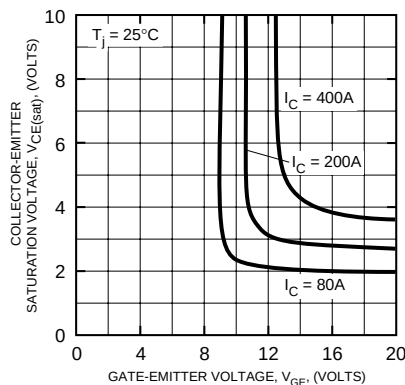
TRANSFER CHARACTERISTICS
(TYPICAL)



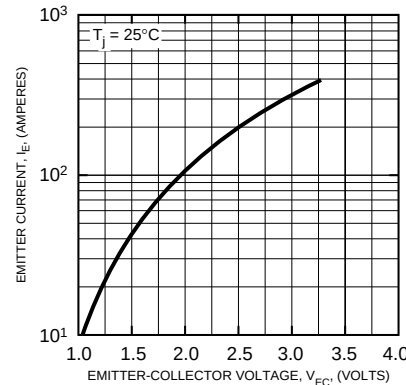
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



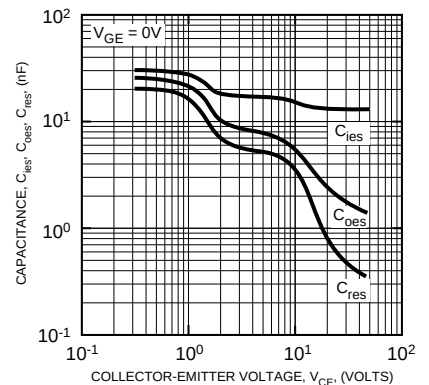
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



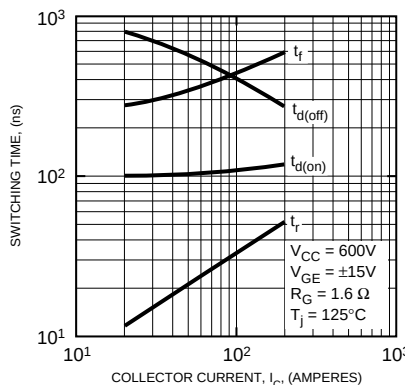
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



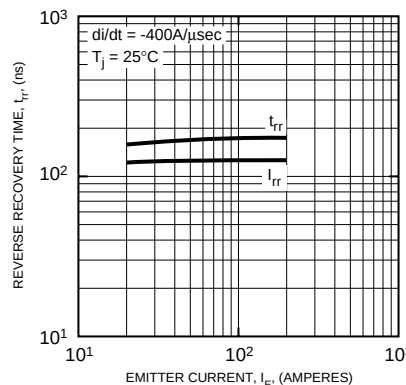
CAPACITANCE VS. Vce
(TYPICAL)



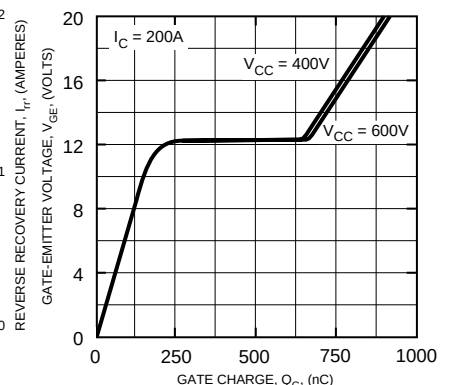
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE, Vge



CM200DU-24H

HIGH POWER SWITCHING USE
INSULATED TYPE

